

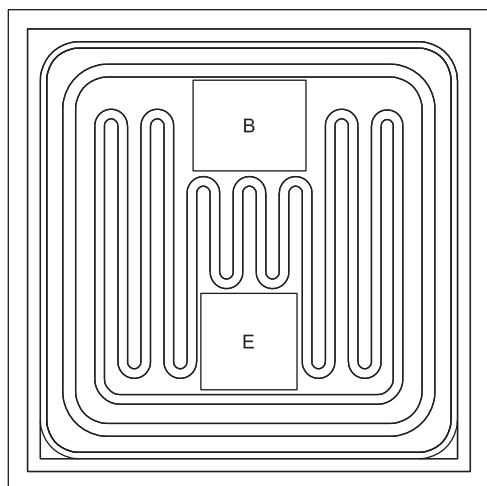
PROCESS CP710
Small Signal Transistor
PNP - High Voltage Transistor Chip



PROCESS DETAILS

Process	EPITAXIAL PLANAR
Die Size	26 x 26 MILS
Die Thickness	9.0 MILS
Base Bonding Pad Area	6.1 x 4.9 MILS
Emitter Bonding Pad Area	5.2 x 5.2 MILS
Top Side Metalization	Al - 30,000Å
Back Side Metalization	Au - 18,000Å

GEOMETRY



BACKSIDE COLLECTOR

R2

GROSS DIE PER 4 INCH WAFER

17,130

PRINCIPAL DEVICE TYPES

CMPTA94

CXTA94

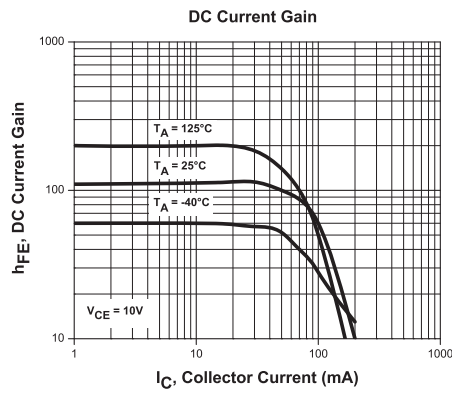
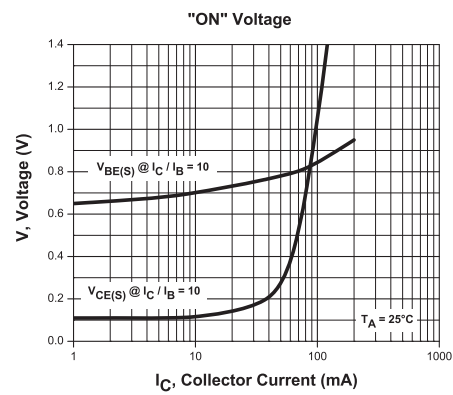
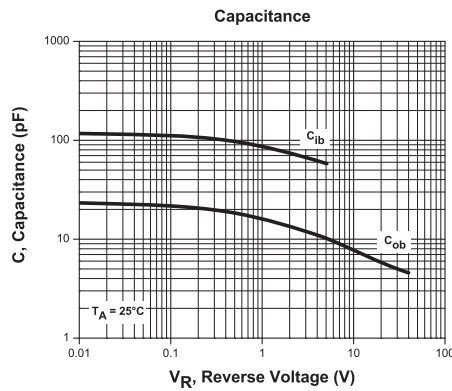
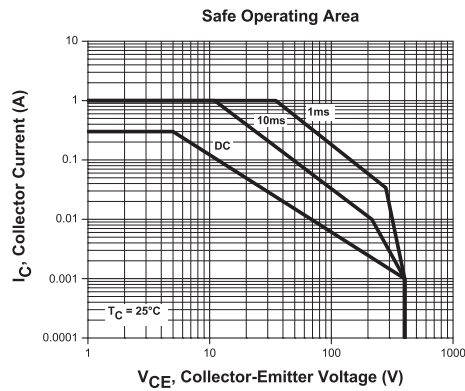
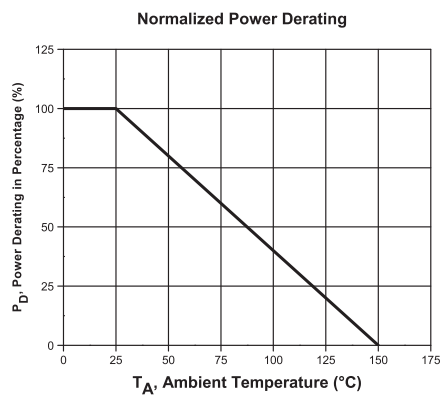
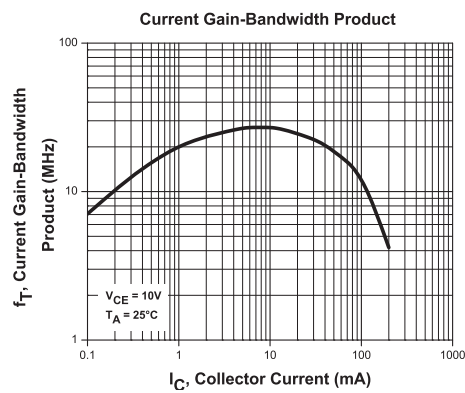
CZTA94

MPSA94

R5 (22-March 2010)

PROCESS CP710

Typical Electrical Characteristics



R5 (22-March 2010)